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# ***Advances in Patterning Materials and Processes XXXII***

**Thomas I. Wallow  
Christoph K. Hohle**  
*Editors*

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- 1    Keynote Session  
     **Christoph K. Hohle**, Fraunhofer Institute for Photonic Microsystems  
     (Germany)
- 2    EUV Resist Extendability: Joint Session with Conferences 9422 and  
     9425  
     **Robert L. Brainard**, College of Nanoscale Science and Engineering  
     (United States)  
     **James W. Thackeray**, Dow Electronic Materials (United States)
- 3    EUV Resist Mechanistic Studies: Joint Session with Conferences 9422  
     and 9425  
     **John J. Biafore**, KLA-Tencor Texas (United States)  
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- 4    Negative Tone Materials  
     **Yoshio Kawai**, Shin-Etsu Chemical Company, Ltd. (Japan)  
     **Clifford L. Henderson**, Georgia Institute of Technology (United States)
- 5    Resist and Process Fundamentals  
     **Ralph R. Dammel**, EMD Performance Materials Corporation  
     (United States)  
     **Robert Allen**, IBM Research - Almaden (United States)
- 6    Patterning Materials and Etch: Joint Session with Conferences 9425  
     and 9428  
     **Qinghuang Lin**, IBM Thomas J. Watson Research Center  
     (United States)  
     **Douglas Guerrero**, Brewer Science, Inc. (United States)
- 7    Materials and Etch in Emerging Technologies: Joint Session with  
     Conferences 9425 and 9428  
     **Christoph K. Hohle**, Fraunhofer Institute for Photonic Microsystems  
     (Germany)  
     **Qinghuang Lin**, IBM Thomas J. Watson Research Center  
     (United States)
- 8    DSA Materials and Processes I: Joint Session with Conferences 9425  
     and 9423  
     **Juan J. de Pablo**, The University of Chicago (United States)  
     **Roel Gronheid**, IMEC (Belgium)

- 9 DSA Materials and Processes II: Joint Session with Conferences 9425 and 9423  
**Todd R. Younkin**, Intel Corporation (United States)  
**Sean D. Burns**, IBM Corporation (United States)
- 10 EUV Resists and Processes  
**Katsumi Ohmori**, Tokyo Ohka Kogyo Company, Ltd. (Japan)  
**Ramakrishnan Ayothi**, JSR Micro, Inc. (United States)
- 11 DSA Materials and New Concepts  
**Mark H. Somervell**, Tokyo Electron America, Inc. (United States)  
**Daniel P. Sanders**, IBM Research - Almaden (United States)
- 12 New Patterning Processes  
**Ralph R. Dammel**, EMD Performance Materials Corporation (United States)  
**Scott W. Jessen**, Texas Instruments Inc. (United States)
- 13 Materials and Process Engineering  
**Thomas I. Wallow**, ASML Brion Technologies (United States)  
**Clifford L. Henderson**, Georgia Institute of Technology (United States)

